ICTE5.0 thru ICTE18C

Vishay General Semiconductor

TRANSZORB® Transient Voltage Suppressors



Case Style 1.5KE

MAJOR RATINGS AND CHARACTERISTICS

V _{WM}	5.0 V to 18 V		
P _{PPM}	1500 W		
PD	6.5 W		
I _{FSM}	200 A		
T _j max.	175 °C		

DEVICES FOR BIDIRECTION APPLICATIONS

For bidirectional types, use C suffix (e.g. ICTE-18C). Electrical characteristics apply in both directions.

FEATURES

Glass passivated chip junction



- Available in Unidirectional and Bidirectional
- 1500 W peak pulse power capability with a 10/1000 μs waveform, repetitive rate (duty cycle): 0.01 %
- Excellent clamping capability
- Very fast response time
- Low incremental surge resistance
- Solder Dip 260 °C, 40 seconds
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

Use in sensitive electronics protection against voltage transients induced by inductive load switching and lighting on ICs, MOSFET, signal lines of sensor units for consumer, computer, industrial and telecommunication.

MECHANICAL DATA

Case: Molded epoxy body over passivated junction Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002B and JESD22-B102D

E3 suffix for commercial grade, HE3 suffix for high reliability grade (AEC Q101 qualified)

Polarity: For unidirectional types the color band denotes cathode end, no marking on bidirectional types

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Peak pulse power dissipation with a 10/1000 μs waveform $^{(1)}$ (Fig. 1)	P _{PPM}	Minimum 1500	W				
Peak pulse current with a 10/1000 μs waveform $^{(1)}$ (Fig. 3)	I _{PPM}	see next table	А				
Power dissipation on infinite heatsink at $T_L = 75 \text{ °C}$ (Fig. 8)	PD	6.5	W				
Peak forward surge current 8.3 ms single half sine-wave unidirectional only $^{(2)}$	I _{FSM}	200	А				
Maximum instantaneous forward voltage at 100 A for unidirectional only	V _F	3.5	V				
Operating junction and storage temperature range	T _J , T _{STG}	- 55 to + 175	°C				

Note:

(1) Non-repetitive current pulse, per Fig. 3 and derated above T_{A} = 25 °C per Fig. 2

(2) 8.3 ms single half sine-wave, duty cycle = 4 pulses per minute maximum

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ELECTRICAL CHARACTERISTICS (JEDEC REGISTERED DATA) (T _A = 25 °C unless otherwise noted)									
JEDEC TYPE NUMBER	GENERAL SEMICONDUCTOR PART NUMBER	STAND-OFF VOLTAGE V _{WM} (V)	MINIMUM ⁽³⁾ BREAKDOWN VOLTAGE AT 1.0 mA V _(BR) (V)	MAXIMUM REVERSE LEAKAGE AT V _{WM} Ι _D (μΑ)	$\label{eq:maximum} \begin{array}{c} \mbox{MAXIMUM}\\ \mbox{CLAMPING}\\ \mbox{VOLTAGE}\\ \mbox{AT }_{IPP} = 1.0 \mbox{ A}\\ \mbox{V}_{C} \mbox{ (V)} \end{array}$	$\begin{array}{l} \text{MAXIMUM} \\ \text{CLAMPING} \\ \text{VOLTAGE AT} \\ \text{I}_{\text{PP}} = 10 \text{ A} \\ \text{V}_{\text{C}} (\text{V}) \end{array}$	MAXIMUM PEAK PULSE CURRENT I _{PP} (A)		
UNIDIRECTIONAL TYPES									
1N6373 ⁽²⁾	ICTE-5 ⁽²⁾	5.0	6.0	300	7.1	7.5	160		
1N6374	ICTE-8	8.0	9.4	25.0	11.3	11.5	100		
1N6375	ICTE-10	10.0	11.7	2.0	13.7	14.1	90		
1N6376	ICTE-12	12.0	14.1	2.0	16.1	16.5	70		
1N6377	ICTE-15	15.0	17.6	2.0	20.1	20.6	60		
1N6378	ICTE-18	18.0	21.2	2.0	24.2	25.2	50		
BIDIRECTIO	BIDIRECTIONAL TYPES								
1N6382	ICTE-8C	8.0	9.4	50.0	11.4	11.6	100		
1N6383	ICTE-10C	10.0	11.7	2.0	14.1	14.5	90		
1N6384	ICTE-12C	12.0	14.1	2.0	16.7	17.1	70		
1N6385	ICTE-15C	15.0	17.6	2.0	20.8	21.4	60		
1N6386	ICTE-18C	18.0	21.2	2.0	24.8	25.5	50		

Note:

(1) "C" Suffix indicates bi-directional

(2) ICTE-5 and 1N6373 are not available as bi-directional

(3) The minimum breakdown voltage as shown takes into consideration the \pm 1 Volt tolerance normally specified for power supply regulation on most integrated circuit manufacturers data sheets. Please consult factory for devices that require reduced clamping voltages where tighter regulated power supply voltages are employed

(4) Clamping Factor: 1.33 at full rated power; 1.20 at 50 % rated power; Clamping Factor: the ratio of the actual V_C (Clamping Voltage) to the $V_{(BR)}$ (Breakdown Voltage) as measured on a specific device

ORDERING INFORMATION							
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE			
ICTE-5-E3/54	0.968	54	1400	13" Diameter Paper Tape & Reel			



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RATINGS AND CHARACTERISTICS CURVES

 $(T_A = 25 \ ^{\circ}C \text{ unless otherwise noted})$

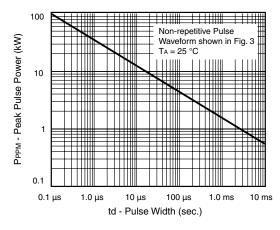


Figure 1. Peak Pulse Power Rating Curve

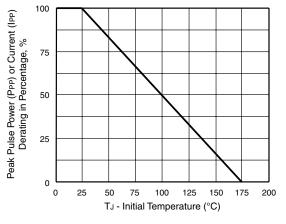


Figure 2. Pulse Power or Current vs. Initial Junction Temperature

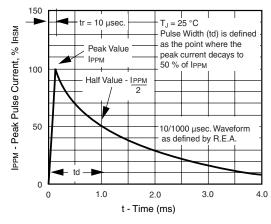


Figure 3. Pulse Waveform

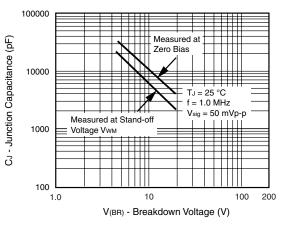


Figure 4. Typical Junction Capacitance Uni-Directional

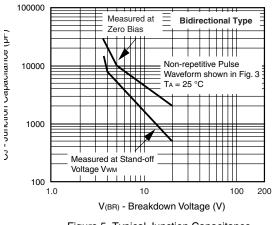
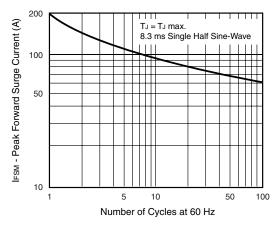
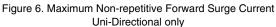


Figure 5. Typical Junction Capacitance





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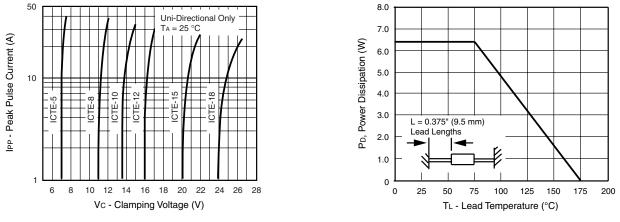
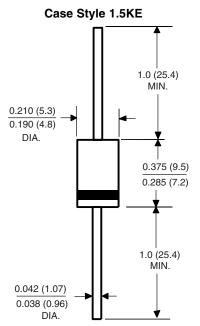


Figure 7. Typical Characteristics Clamping Voltage

Figure 8. Power Derating Curve

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